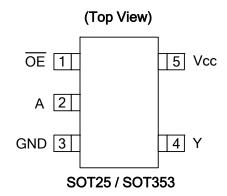


## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Description

The 74AHCT1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output enable ( $\overline{OE}$ ) pin. The device is designed for operation with a power supply range of 4.5V to 5.5V.

### **Pin Assignments**



### Features

- Supply Voltage Range from 4.5V to 5.5V
- ± 8 mA Output Drive at 5.0V
- CMOS low power consumption
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time.
- ESD Protection per JESD 22
  - o Exceeds 200-V Machine Model (A115-A)
  - Exceeds 2000-V Human Body Model (A114-A)
  - Exceeds 1000-V Charged Device Model (C101C)

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at

Latch-Up Exceeds 100mA per JESD 78, Class II

http://www.diodes.com/products/lead\_free.html.

- SOT25 and SOT353: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)

### Applications

- General Purpose Logic
- Wide array of products such as:
  - o PCs, networking, notebooks, netbooks, PDAs
  - o Computer peripherals, hard drives, CD/DVD ROM
  - o TV, DVD, DVR, set top box
  - o Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders

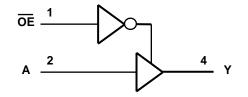


# SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### **Pin Descriptions**

Pin Name Pin No.		Description	
ŌE	1	Output Enable	
А	2	Data Input	
GND	3	Ground	
Y 4		Data Output	
V <sub>CC</sub> 5		Supply Voltage	

### Logic Diagram



## **Function Table**

Inp	Output	
OE	Α	Y
L	Н	Н
L	L	L
Н	Х	Z



# SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current VI<0	-20	mA
Ι <sub>ΟΚ</sub>	Output Clamp Current ( $V_O < 0$ or $V_O > V_{CC}$ )	±20	mA
Ι <sub>Ο</sub>	Continuous output current ( $V_0 = 0$ to $V_{CC}$ )	±25	mA
I <sub>CC</sub>	Continuous current through V <sub>CC</sub>	50	mA
I <sub>GND</sub>	Continuous current through GND	-50	mA
T <sub>J</sub> Operating Junction Temperature		-40 to 150	°C
T <sub>STG</sub> Storage Temperature		-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

### **Recommended Operating Conditions (Note 3)**

Symbol		Parameter	Min	Max	Unit
V <sub>CC</sub>	Operating Voltage		4.5	5.5	V
V <sub>IH</sub>	High-level Input Voltage		2.0		V
VIL	Low-level input voltage			0.8	V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V <sub>CC</sub>	V
I <sub>ОН</sub>	High-level output current			-8	mA
I <sub>OL</sub>	Low-level output current			8	mA
Δt/ΔV	Input transition rise or fall rate			20	ns/V
T <sub>A</sub>	Operating free-air temperature		-40	125	٥C

Notes: 3. Unused inputs should be held at V<sub>CC</sub> or Ground.



# SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Electrical Characteristics**

Cumhal	Deremeter	Test Conditions	V		25ºC		-40°C to 85°C		-40°C to 125°C		11
Symbol	bol Parameter Test Conditions		V <sub>CC</sub>	Min	Тур.	Max	Min	Max	Min	Max	Unit
.,	High Level	I <sub>OH</sub> = -50μA	4.5V	4.4	4.5		4.4		4.4		
V <sub>OH</sub>	Output Voltage	I <sub>OH</sub> = -8mA	4.5V	3.94			3.8		3.70		V
Max	Low Level	I <sub>OL</sub> = 50μA	4.5V		0	0.1		0.1		0.1	V
V <sub>OL</sub>	Output Voltage	$I_{OL} = 8mA$	4.5V			0.36		0.44		0.55	V
lı –	Input Current	$V_1 = 5.5V$ or GND	0 to 5.5V			±0.1		±1		±2	μA
I <sub>OZ</sub>	Z State Leakage Current	V <sub>O</sub> =0 to 5.5V	5.5V			0.25		2.5		10	μΑ
I <sub>CC</sub>	Supply Current	V <sub>I</sub> = 5.5V or GND I <sub>O</sub> =0	5.5V			1		10		40	μA
Ci	Input Capacitance	V <sub>I</sub> = V <sub>CC</sub> – or GND	5.5V		2.0	10		10		10	pF
ΔI <sub>CC</sub>	Additional Supply Current	One input at 3.4 V Other inputs at V <sub>CC</sub> or GND	5.5V			1.35		1.5			mA
Thermal Resistance		SOT25			204						°044
$\theta_{JA}$	Junction-to- Ambient	SOT353	(Note 4)		371						°C/W
	Thermal Resistance Junction-to- Case	SOT25			52						
θ <sub>JC</sub>		SOT353	(Note 4)		143						°C/W

Note: 4. Test conditions for SOT25, and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



# SINGLE BUFFER GATE WITH 3-STATE OUTPUT

# **Switching Characteristics**

#### $V_{cc} = 5V \pm 0.5V$ (see Figure 1)

Parameter	From	то			25⁰C		-40°C t	o 85ºC	-40°C to	o 125⁰C	Unit	
Farameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit	
+ .	Δ	V	C <sub>L</sub> =15pF	0.6	3.4	5.5	0.6	6.5	0.6	7.0	ns	
t <sub>pd</sub>	A	Ŷ	$C_L=50pF$	0.6	4.7	7.5	0.6	8.5	0.6	9.5	ns	
	ŌE	v	C <sub>L</sub> =15pF	0.6	3.6	5.6	0.6	6.3	0.6	7.0	ns	
t <sub>en</sub>	OE	OE	ř	C <sub>L</sub> =50pF	0.6	5.4	8.0	0.6	9.0	0.6	9.5	ns
		V	C <sub>L</sub> =15pF	0.6	4.3	6.8	0.6	8.0	0.6	8.5	ns	
t <sub>dis</sub>	OE	ř	C <sub>L</sub> =50pF	0.6	6.1	8.8	0.6	10.0	0.6	11.0	ns	

### **Operating Characteristics**

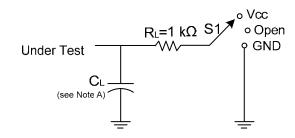
### $T_A = 25 \ ^{o}C$

Parameter		Test Conditions	V <sub>CC</sub> = 5 V Typ.	Unit
C <sub>pd</sub>	Power dissipation capacitance	f = 1 MHz No Load	14	pF



# SINGLE BUFFER GATE WITH 3-STATE OUTPUT

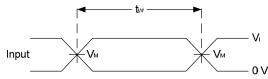
### **Parameter Measurement Information**



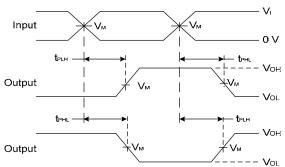
TEST	S1	
t <sub>PLH</sub> /t <sub>PHL</sub>	Open	
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vload	
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND	

Vee	Inputs		V	C	MA	
Vcc	VI	t <sub>r</sub> /t <sub>f</sub>	VM VM	υL	VΔ	
5V±0.5V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	15pF	0.3V	
5V±0.5V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	50pF	0.3V	

Output



#### **Voltage Waveform Pulse Duration**



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

#### Vм Vм Control 0 V Output tezi – te VLOAD/2 Waveform 1 S1 at VLOAD Vol + Va (see Note B) · Voi → t<sub>РZH</sub> → 🗲 tenz Output Vон Waveform 2 Vон V ∠∨м S1 at GND (see Note B) 6 OV

#### Voltage Waveform Enable and Disable Times Low and High Level Enabling

#### Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

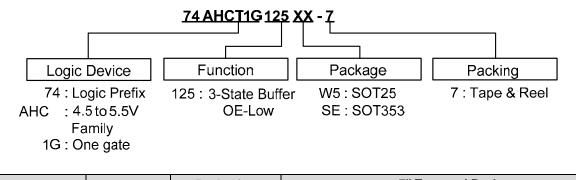
- B. All pulses are supplied at pulse repetition rate  $\leq$  1 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$
- E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{EN}$ .
- F.  $t_{\text{PLH}}$  and  $t_{\text{PHL}}$  are the same as  $t_{\text{PD.}}$

Vi



# SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### **Ordering Information**



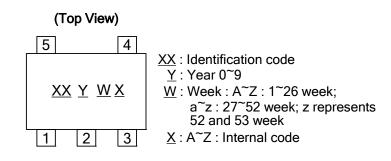
0	
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2

	Device Package		Packaging	7" Tape and Reel		
	Device	Code	(Note 5)	Quantity	Part Number Suffix	
Pb,	74AHCT1G125W5-7	W5	SOT25	3000/Tape & Reel	-7	
Pb,	74AHCT1G125SE-7	SE	SOT353	3000/Tape & Reel	-7	

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

### **Marking Information**



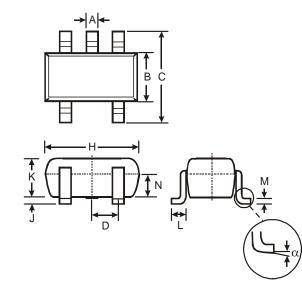
Part Number	Package	Identification Code
74AHCT1G125W5	SOT25	ZY
74AHCT1G125SE	SOT353	ZY



# SINGLE BUFFER GATE WITH 3-STATE OUTPUT

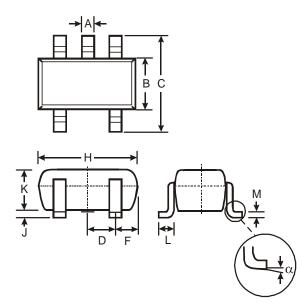
### Package Outline Dimensions (All Dimensions in mm)

### (1) Package Type: SOT25



SOT25				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
В	1.50	1.70	1.60	
С	2.70	3.00	2.80	
D			0.95	
Н	2.90	3.10	3.00	
J	0.013	0.10	0.05	
Κ	1.00	1.30	1.10	
L	0.35	0.55	0.40	
М	0.10	0.20	0.15	
Ν	0.70	0.80	0.75	
α	0°	8°	_	
All Dimensions in mm				

### (2) Package Type: SOT353



SOT353				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65 Typ			
F	0.40	0.45		
Н	1.80	2.20		
J	0	0.10		
К	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				





### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

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